## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# BTA212B series D, E and F Three quadrant triacs guaranteed commutation

Product specification

October 2003



# Three quadrant triacs guaranteed commutation

### BTA212B series D, E and F

### **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope suitable for surface mounting intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

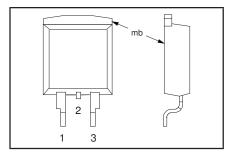
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX	UNIT	
	BTA212B- BTA212B- BTA212B-	600D 600E 600F	800E		
$V_{DRM}$	Repetitive peak off-state	600	800	V	
I <sub>T(RMS)</sub> I <sub>TSM</sub>	voltages RMS on-state current Non-repetitive peak on-state current	12 95	12 95	A A	

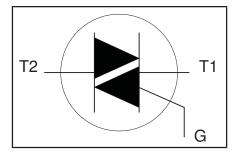
### **PINNING - SOT404**

PIN	DESCRIPTION			
1	main terminal 1			
2	main terminal 2			
3	gate			
mb	main terminal 2			

### **PIN CONFIGURATION**



### **SYMBOL**



### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	M	AX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave;	-	-	12	Α
I <sub>TSM</sub>	Non-repetitive peak on-state current	$T_{mb} \le 99$ °C full sine wave; $T_{j} = 25$ °C prior to surge t = 20 ms			95	A
l <sup>2</sup> t	124 for the class	t = 16.7 ms	-	1	05	A A <sup>2</sup> s
dl <sub>T</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	$I_{TM} = 10 \text{ ms}$ $I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A};$ $I_{G} = 0.2 \text{ A}$	-		45 00	A'μs
$\begin{matrix} I_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	triggering Peak gate current Peak gate power Average gate power	over any 20 ms	- - -		2 5 ).5	A W W
T <sub>stg</sub>	Storage temperature Operating junction temperature	period	-40 -	1	50 25	Ç

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air		- - 55	1.5 2.0 -	K/W K/W K/W

### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA212B-	D	D	E	F	
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$		_			
		T2+ G+ T2+ G-	-	5 5 5	10 10	25 25	mA mA
1.		T2- G-	-	5	10	25	mA
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ $T2 + G +$ $T2 + G -$	-	15 25	25 30	30 40	mA mA
		T2+ G- T2- G-	-	25	30	40	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	25	30	mA
					D, E, F		
$V_{T}$	On-state voltage Gate trigger voltage	$I_T = 17 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-		1.6 1.5		<<
V GT	Gate ingger voltage	$V_D = 12 \text{ V}, I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$ $I_T = 125 \text{ °C}$	0.25		-		V
I <sub>D</sub>	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125 ^{\circ}C$	-		0.5		mA

### **DYNAMIC CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.	UNIT	
		BTA212B-	D	Е	F		
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110 ^{\circ}C;$ exponential waveform; gate open circuit	20	60	70	-	V/µs
dI <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 10 \text{V}/\mu\text{s};$ gate open circuit	1.0	8	21	-	A/ms
dI <sub>com</sub> /dt	Critical rate of change of commutating current	$\begin{array}{l} V_{\text{DM}} = 400 \text{ V; } T_{j} = 125 \text{ °C;} \\ I_{\text{T(RMS)}} = 12 \text{ A;} \\ dV_{\text{com}}/dt = 0.1 \text{V/}\mu\text{s; gate} \\ \text{open circuit} \end{array}$	3.5	16	32	-	A/ms

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<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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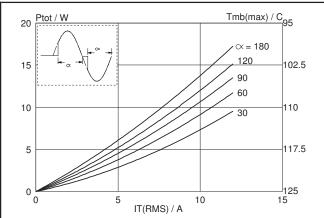


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

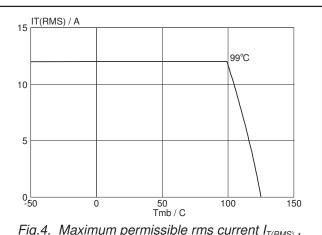


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

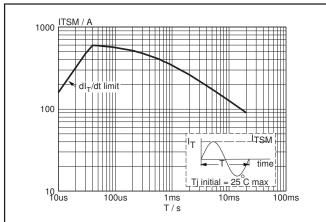


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

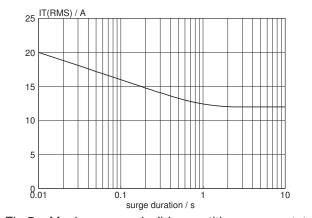


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 99 ^{\circ}C$ .

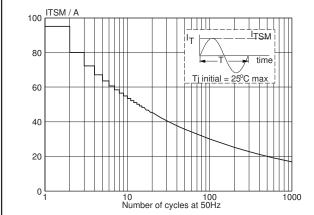
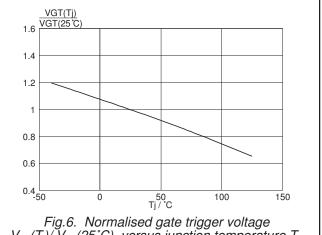


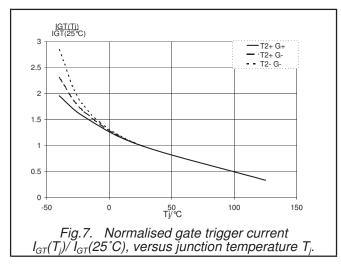
Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

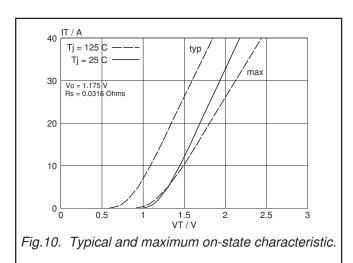


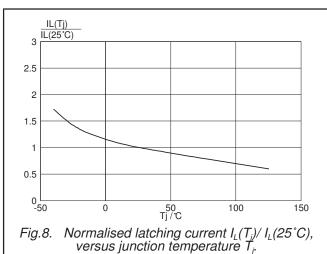
 $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_i$ .

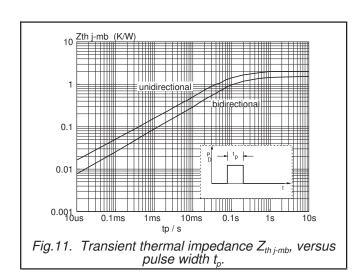
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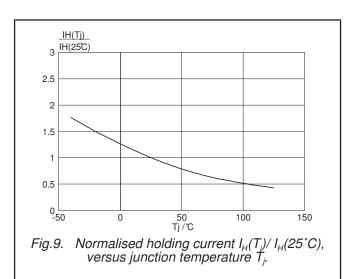
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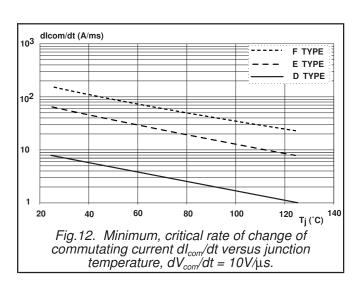








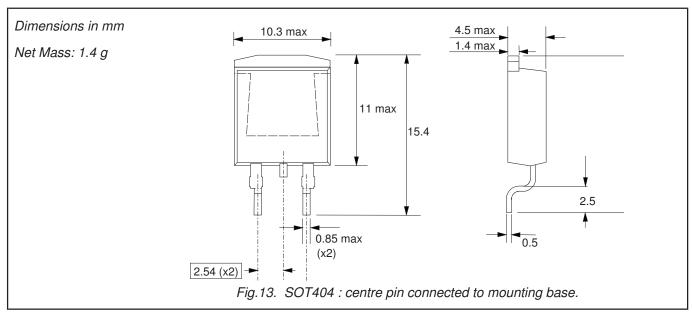




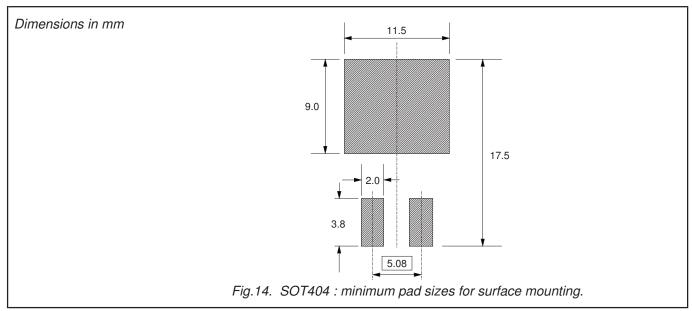
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### **MECHANICAL DATA**



### **MOUNTING INSTRUCTIONS**



### **Notes**

1. Plastic meets UL94 V0 at 1/8".

### Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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